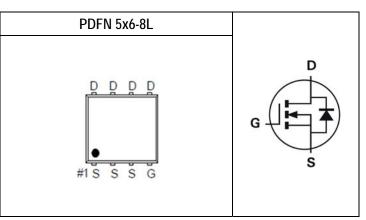


DG60N05HQ

DG-FET™ 60V N-Channel Power MOSFET

Key Performance Parameters							
Parameter Value Unit							
V _{DSS}	60	V					
RDS(ON) max. VGS=10V	2.6	mΩ					
lo	50.0	А					
Qg	69.1	nC					
Q _{gd}	21.9	nC					
Qsw	30.1	nC					
$Q_{g(sync)}$	47.2	nC					



Features	Application
Optimized for synchronous rectification	Battery powered circuits
Low Input Capacitance	BLDC Motor drive applications
Low Switching Charge	 Half-bridge and full-bridge topologies
Low Miller Capacitance	Synchronous rectifier applications
Fully Characterized Capacitance and Avalanche	Resonant mode power supplies
 Pb-free lead plating; RoHS compliant 	

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
DG60N05HQ	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	3,000

Absolute Maximum Ratings (T_=25°C unless otherwise noted)

Parameter			ol	Value	Unit
Drain-Source Voltage		V _{DS}		60	V
Gate-Source Voltage		V _{GS}		±20	V
Drain Current-Continuous	T _C =25°C			50.0	А
Drain Current-Continuous	Tc=100°C	ID		31.6	А
Drain Current-Pulsed Note 1	Tc=25°C	Ідм		151	А
Avalanche Current		IAR		38	А
Single Pulse Avalanche Energy Note 3		EAS		72	mJ
Maximum Power Dissipation	Tc=25°C	Ptot		11.5	W
Operating and Storage Temperature Ra	nge	TJ,		150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Thermal resistance, Junction-to-Ambient Note 2	$R_{ heta JA}$	Steady State	-	62	-	°C/W
Thermal resistance, Junction-to-Case	Rөлс	Steady State	-	10.9	-	°C/W

Notes:

1. Pulse Test: Pulse Width \leq 10ms, Duty Cycle \leq 1%.

 R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. For surface-mounted packages, both R_{BJA} and R_{BJC} are measured with the device mounted on approximately 1"×1" FR-4 PCB. In actual applications, the PCB layout may greatly affect the thermal resistance and current-carrying capability of the device-board assembly.

3. Starting TJ=25°C, VD=30V, L=0.1mH, VG=10V, Rated VDS =60V N-CH.



DG-FET™ 60V N-Channel Power MOSFET

Electrical Characteristics (TJ=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V _(BR) DSS	V _{GS} =0V, I _{DS} =250uA	60	-	-	V
Zara Cata Valtaga Drain Current	,	V _{DS} =48V, V _{GS} =0V, T _J =25°C	-	-	10	μA
Zero Gate Voltage Drain Current	IDSS	V _{DS} =48V, V _{GS} =0V, T _J =125°C	-	-	100	μA
Gate-Body Leakage	lgss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

STATIC CHARACTERISTICS

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	2	2.6	3.4	V
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =10V, I _{DS} =50A	-	-	2.6	mΩ
Gate Resistance	R_{g}	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.1	2	Ω
Forward Transconductance	g _{fs}	V _{DS} =5V, I _{DS} =20A	-	12	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	3815	-	pF
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	1866	-	pF
Reverse Transfer Capacitance	Crss		-	132	-	pF
Turn-On Delay Time	T _{d(on)}		-	18.6	-	ns
Rise Time	tr	V_{DS} =30V, V_{GS} =10V, I_{DS} =50A, R_{GEN} =4.7 Ω	-	72.6	-	ns
Turn-Off Delay Time	T _{d(off)}		-	39.7	-	ns
Fall Time	tr		-	39.4	-	ns

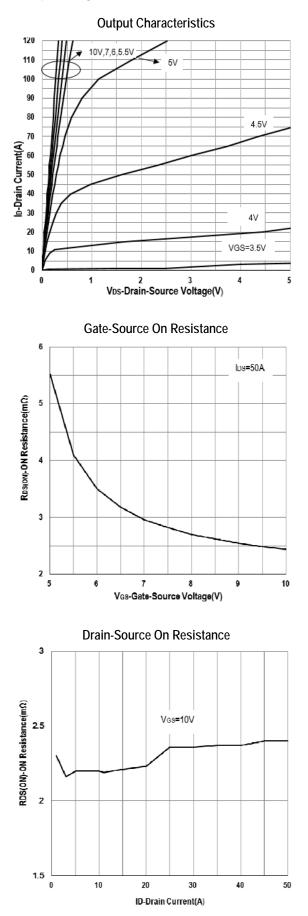
GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate to Source Gate Charge	Qgs	V _{DD} =30V, I _D =50A	-	18.5	-	nC
Gate charge at threshold	Qg(th)	V _{DD} =30V, I _D =50A	-	10.3	-	nC
Gate to Drain Charge	Q_{gd}	V _{DD} =30V, I _D =50A	-	21.9	-	nC
Switching charge	Qsw	V _{DD} =30V, I _D =50A	-	30.1	-	nC
Gate charge total	Q_g	V_{DD} =30V, I_D =50A, V_{GS} =0 to 10V	-	69.1	-	nC
Gate plateau voltage	Vplateau	V _{DD} =30V, I _D =50A	-	4.83	-	V
Gate charge total, sync. FET (Qg- Qgd)	Qg(sync)	V _{DS} =0.1V	-	47.2	-	nC

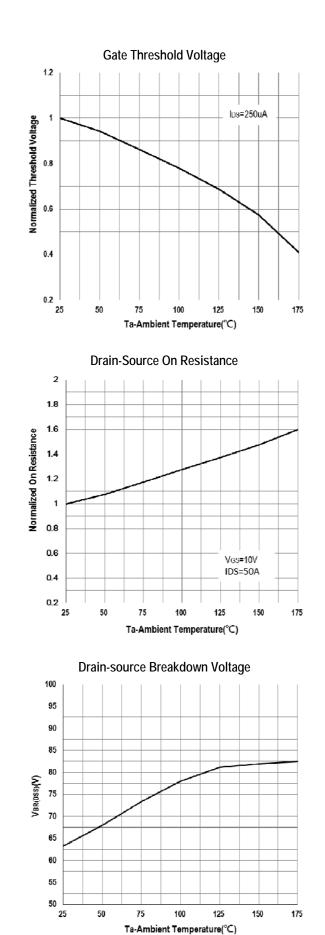
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions Min. Typ. M		Max.	Unit	
Diode Forward Voltage	Vsd	V _{GS} =0V, I _F =50A	-	-	1.3	V
Redy Diede Deverse Desevery Time	tır	V _{DD} =48V, I _F =50A, di/dt=100A/µs	-	60.6	-	ns
Body Diode Reverse Recovery Time		V _{DD} =48V, I _F =50A, di/dt=200A/µs	-	46.1	-	ns
Redy Diede Deverse Reservery Charge	0	V _{DD} =48V, I _F =50A, di/dt=100A/µs	-	72.3	-	nC
Body Diode Reverse Recovery Charge	Qrr	V _{DD} =48V, I _F =50A, di/dt=200A/µs	-	116.1	-	nC
Reverse Recovery Current	loov	V _{DD} =48V, I⊧=50A, di/dt=100A/µs	-	2.1	-	Α
	IRRM	V _{DD} =48V, I _F =50A, di/dt=200A/µs	-	4.4	-	Α



DG60N05HQ DG-FET™ 60V N-Channel Power MOSFET

Typical Operating Characteristics

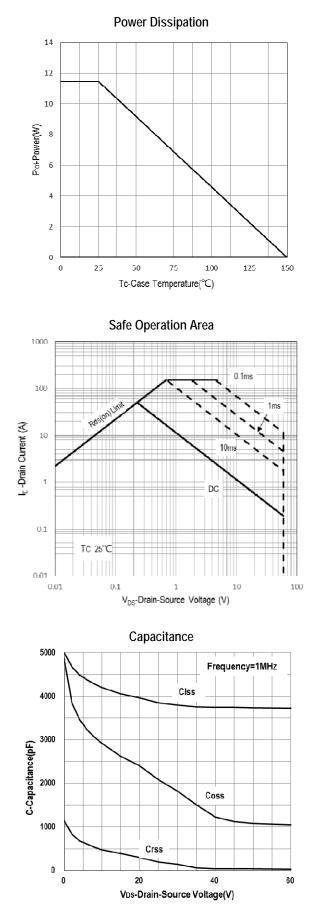


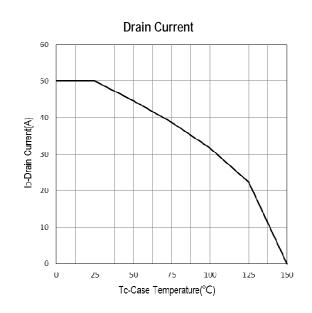




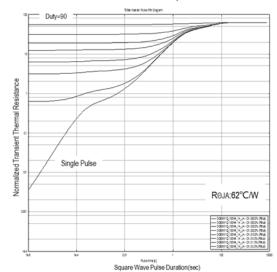
DG60N05HQ DG-FET™ 60V N-Channel Power MOSFET

Typical Operating Characteristics (Cont.)

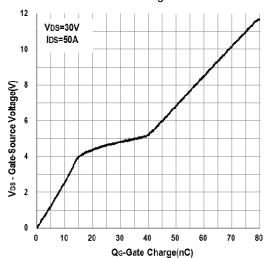




Transient Thermal Impedance



Gate Charge



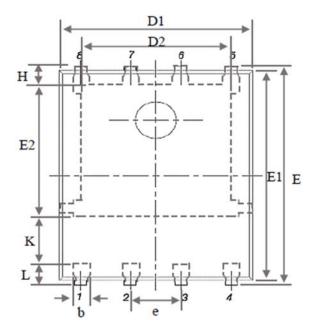


Marking Information

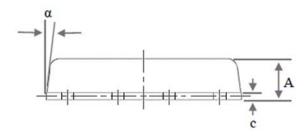
PDFN 5x6-8L (Q)	Marking Rule
PDFN 5x6-8L (Q) Laser Marking DG60N05HQ YYMMXXX	Marking Rule Line 1 : Device Name DG60N05HQ Line 2 : Date Code YYMMXXX YY : Year Code MM : Month
	XXX:Serial Number



Package of Dimension



Symbol	Min	Nor	Max
Α	0.90	1.04	1.17
b	0.33	0.42	0.51
С	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e		1.27 BSC	
Н	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25



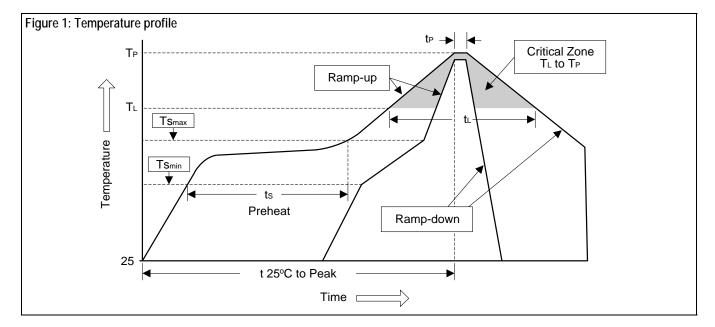
1. All dimension are in millimeters.

2. Dimension dose not include burrs and mold flash/protrusions.



Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t _P)	10 to 50 sec	2010 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

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